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(71) Applicant *(for all designated States except US)*: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Sunnyvale, CA 94088-3453 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **WIRBELEIT, Frank** [DE/DE]; Lindenweg 17, 09599 Freiberg (DE). **BURBACH, Gert** [DE/DE]; Warnemuender Strasse 5A, 01109 Dresden (DE). **WIECZOREK, Karsten** [DE/DE]; Am Schulfeld 24, 01109 Dresden (DE). **HORSTMANN, Manfred** [DE/DE]; Aeussere Parkstrasse 25, 01833 Duerroehrsdorf-Dittersbach (DE).

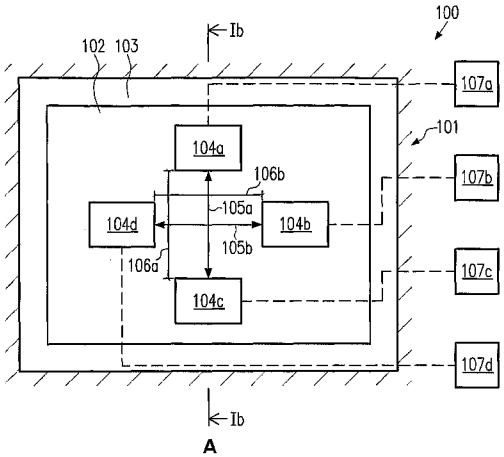
(74) Agent: **DRAKE, Paul, S.**; Advanced Micro Devices, Inc., 5204 East Ben White Boulevard, Mail Stop 562, Austin, TX 78741 (US).

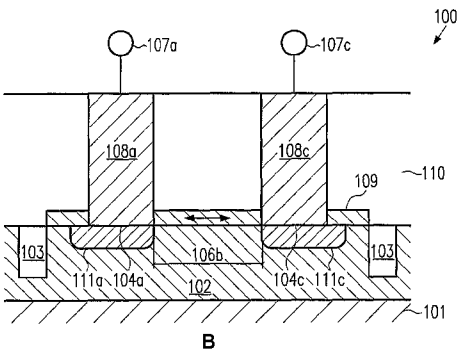
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(54) Title: TECHNIQUE FOR EVALUATING LOCAL ELECTRICAL CHARACTERISTICS IN SEMICONDUCTOR DEVICES





(57) Abstract: By providing a test structure (100) including a plurality of test pads (104), the anisotropic behavior of stress and strain influenced electrical characteristics, such as the electron mobility, may be determined in a highly efficient manner. Moreover, the test pads (104) may enable the detection of stress and strain induced modifications with a spatial resolution in the order of magnitude of individual circuit elements.

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